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FAX

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Date: November 21, 2002

Pages (including cover): 3

To: April Wise

Fax: 703.746.8822

Ph:

From: Donald R. Studebaker

Message: RE: U.S. Patent Application No. 09/865,546

Dear Ms. Wise:

In response to the Notice of Non-Compliant Amendment, attached please find a clean version of the paragraph in question in connection with the Amendment filed October 1, 2002.

Application No.: 09/865,546
Attorney Docket No.: 740819-560
Art Unit 2829
Page 4

On page 9, please replace the final paragraph abridging pages 9 and 10 with the following substitute paragraph. Attached hereto is a marked-up copy of the substitute paragraph.

N/E
--In the second semiconductor device, the heavily-doped diffusion layer preferably corresponds to a pocket heavily-doped diffusion layer of a MIS semiconductor device, and the MIS semiconductor device preferably includes a gate electrode formed above the semiconductor substrate with a gate insulating film sandwiched therebetween; a source/drain heavily-doped diffusion layer of a first conductivity type formed in a source/drain region of the semiconductor substrate at a distance from a region below a side face of the gate electrode; an extension region heavily-doped diffusion layer of the first conductivity type formed in the semiconductor substrate between the source/drain heavily-doped diffusion layer and the region below the side face of the gate electrode and having shallower junction than the source/drain heavily-doped diffusion layer; and the pocket region of heavily-doped diffusion layer of a second conductivity type formed in the semiconductor substrate under the extension heavily-doped diffusion layer.--

On page 10, please replace the first full paragraph with the following substitute paragraph. Attached hereto is a marked-up copy of the substitute paragraph.

--In this case, the extension region heavily-doped diffusion layer is preferably formed by using an antimony ion as a dopant.--

On page 10, please replace the third full paragraph with the following substitute paragraph. Attached hereto is a marked-up copy of the substitute paragraph.

B'
--Since a pocket region of heavily-doped diffusion layer is formed by implantation and

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diffusion of the dopant heavy ion in the epitaxial region of silicon in the first method for fabricating a semiconductor device, the heavy ion is minimally segregated in the region below the original amorphous-crystal interface. Accordingly, the semiconductor device can be refined with a leakage current derived from the segregation suppressed.--

N.E.

On page 11, please replace the second full paragraph with the following substitute paragraph. Attached hereto is a marked-up copy of the substitute paragraph.

--In the first method for fabricating a semiconductor device, the heavily-doped diffusion layer is preferably formed by using, as the dopant ion, an indium ion at a dose of $5 \times 10^3/\text{cm}^2$ or more. Since the first dopant layer can be thus changed into an amorphous layer, the channeling of the second dopant subsequently implanted can be suppressed. Accordingly, the extension region heavily-doped diffusion layer and the pocket region of heavily-doped diffusion layer can definitely attain shallow junction, resulting in realizing a semiconductor device with high driving power.--

On page 11, please replace the final paragraph abridging pages 11 and 12 with the following substitute paragraph. Attached hereto is a marked-up copy of the substitute paragraph.

--In the first method for fabricating a semiconductor device, the heavily-doped diffusion layer preferably corresponds to a pocket region of heavily-doped diffusion layer of a MIS semiconductor device, and the method for fabricating the MIS semiconductor device preferably includes the steps of forming a gate electrode above the epitaxial region with a gate insulating film sandwiched therebetween; forming a first dopant layer to be used as the pocket region of